

BYV34-600 Dual rectifier diode ultrafast Rev. 02 — 28 September 2018

Product data sheet

1. **Product profile**

1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

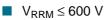
1.2 Features

- Fast switching
- Soft recovery characteristic
- Low switching loss

1.3 Applications

Output rectifiers in high frequency switched-mode power supplies

1.4 Quick reference data



V_F ≤ 1.16 V

Low forward voltage drop High thermal cycling performance

Low thermal resistance

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- I_{O(AV)} ≤ 20 A t_{rr} ≤ 60 ns

Pinning information 2.

Table 1. **Pinning**

| Pin | Description | Simplified outline | Symbol |
|-----|------------------------|--------------------|----------|
| 1 | anode 1 | | |
| 2 | cathode | mb | |
| 3 | anode 2 | <u>ک</u> ک | |
| mb | mounting base; cathode | | _ sym084 |

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3. Ordering information

| Table 2. Ordering information | | | | | | | | | |
|-------------------------------|----------|--|---------|--|--|--|--|--|--|
| Type number | Package | | | | | | | | |
| | Name | Description | Version | | | | | | |
| BYV34-600 | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 | | | | | | |

4. Limiting values

Table 3.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|--|--|-----|------|------|
| V _{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V _{RWM} | crest working reverse voltage | | - | 600 | V |
| V _R | reverse voltage | square waveform; δ = 1.0; T _{mb} \leq 138 °C | - | 600 | V |
| I _{O(AV)} | average output current | square waveform; δ = 0.5; T _{mb} ≤ 107 °C; both diodes conducting | - | 20 | A |
| I _{FRM} | repetitive peak forward current | t = 25 μ s; square waveform; δ = 0.5; T _{mb} \leq 107 °C; per diode | - | 20 | A |
| I _{FSM} | non-repetitive peak forward current | t = 10 ms; sinusoidal waveform; per diode | - | 120 | A |
| | | t = 8.3 ms; sinusoidal waveform; per diode | - | 132 | А |
| T _{stg} | storage temperature | | -40 | +150 | °C |
| T _i | junction temperature | | - | 150 | °C |

5. Thermal characteristics

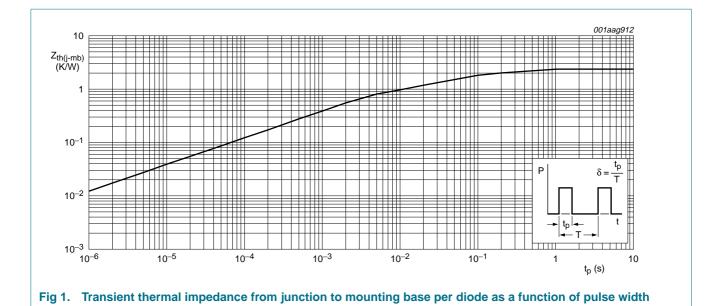
Table 4. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | with heatsink compound; per diode; see <u>Figure 1</u> | - | - | 2.4 | K/W |
| | | with heatsink compound; both diodes conducting | - | - | 1.6 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 60 | - | K/W |

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6. Characteristics

Table 5.Characteristics

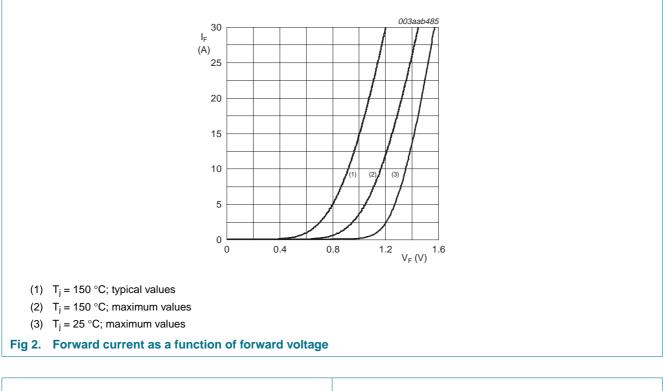
 $T_i = 25 \circ C$ unless otherwise specified.

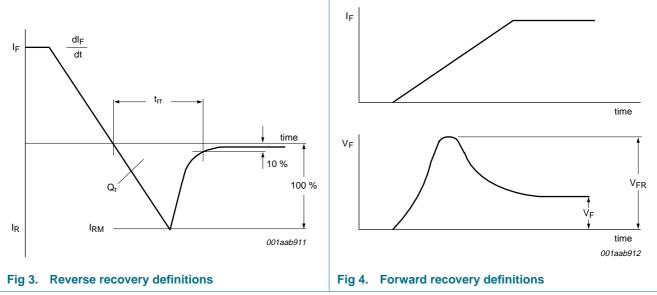
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------------|----------------------------------|---|-----|------|------|------|
| Static cha | racteristics | | | | | |
| V _F forward voltage | | I _F = 10 A; T _j = 150 °C; see <u>Figure 2</u> | - | 0.92 | 1.16 | V |
| | | I _F = 20 A; see <u>Figure 2</u> | - | 1.07 | 1.48 | V |
| I _R | reverse current | V _R = 600 V | - | 10 | 50 | μΑ |
| | | V_R = 600 V; T_j = 100 °C | - | 0.2 | 0.6 | mA |
| Dynamic o | haracteristics | | | | | |
| Qr | recovered charge | $I_F = 2 \text{ A to } V_R \ge 30 \text{ V}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s};$ see Figure 3 | - | 40 | 70 | nC |
| t _{rr} | reverse recovery time | $I_F = 1 A \text{ to } V_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A}/\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{2}$ | - | 50 | 60 | ns |
| I _{RM} | peak reverse recovery current | $\label{eq:l_F} \begin{array}{l} I_F = 10 \ A \ to \ V_R \geq 30 \ V; \\ dI_F/dt = 50 \ A/\mu s; \ T_j = 100 \ ^\circ C; \\ see \ \underline{Figure \ 3} \end{array}$ | - | 3 | 5 | A |
| V _{FR} | forward recovery voltage | I _F = 10 A; dI _F /dt = 10 A/μs; see <u>Figure 4</u> | - | 3.2 | - | V |

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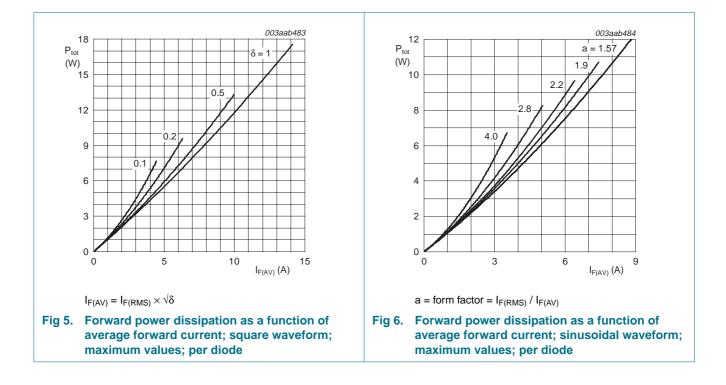




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7. Package outline

| | | | | | | + + _ | | | | | unting ase | | • c | | | | |
|------|----------------|-----------------------------|---------------|----------------|--------------|-------------------|----------------|-------------|-----------|--------------|----------------|------------------------|------------|------------|------------|------------|--|
| | | | | | | | 0 | | 5 1ale | 0 mm பப | | | | | | | |
| UNIT | IONS (n A | nm are ti A ₁ | ne origi b | nal dime b1 | nsions) c | D | D ₁ | E | e | L | L ₁ | L ₂ max. | р | q | Q | | |
| mm | 4.7 4.1 | 1.40 1.25 | 0.9 0.6 | 1.45 1.00 | 0.7 0.4 | 16.0 15.2 | 6.6 5.9 | 10.3 9.7 | 2.54 | 15.0 12.8 | 3.30 2.79 | 3.0 | 3.8 3.5 | 3.0 2.7 | 2.6 2.2 | | |
| | | | REFERENCES | | | | | | | | | | | OPEAN | | ISSUE DATE | |
| | TLINE RSION | - | IE | ~ | | JEDEC | 1 | JEITA | | | | | | | J | ISSUE DATE | |

Fig 7. Package outline SOT78 (3-lead TO-220AB)

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8. Revision history

| Table 6. Revision | n history | | | |
|-------------------|-----------------|-------------------------|---------------|-------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| BYV34-600 V.2 | 20180928 | Product data sheet | - | BYV34-600_1 |
| Modification: | Change from NXF | version to WeEn Version | | |
| BYV34-600_1 | 20071004 | Product data sheet | - | - |

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9. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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